

REMARKS

Reconsideration and allowance of the subject application are respectfully solicited.

Claims 1, 9, and 11 are pending, with Claim 1 being independent.

Applicants wish to thank the Examiner for the courtesies extended in granting and conducting a personal interview with Applicants' representative on April 10, 2007. At the interview, Applicants' representative and the Examiner discussed the outstanding rejection of Claims 1, 9, and 11 under 35 U.S.C. § 103 over US 2004/0201048 A1 (Seki, et al.) in view of U.S. Patent No. 5,470,760 (Nakai) and US 2002/0187312 A1 (Fonash, et al.), which is respectfully traversed.

In more detail, Claim 1 recites, *inter alia*, (a) forming partition walls from a resin composition containing carbon black, in combination with (b) performing a plasma treatment by irradiating the substrate subjected to the dry etching process with plasma in an atmosphere formed by introducing a mixture of a halogen gas as claimed and O₂ gas wherein the amount of O₂ gas is not greater than 30%, each partition wall shows a surface having a contact angle of not smaller than 110° and Ra of between 3nm and 50nm which is greater than before the dry etching and the substrate shows a surface having a contact angle of not greater than 20°.

However, Applicants respectfully submit that none of Seki, et al., Nakai, and Fonash, et al., even in the proposed combinations, assuming, *arguendo*, that such could be combined, discloses or suggests at least the above-discussed combination of claimed features as recited, *inter alia*, in Claim 1.

As discussed at the interview, Applicants respectfully submit that Seki, et al.'s 4th embodiment discussed at [0178] does not state that the claimed dry etching process is performed prior to the use of CF₄/O₂ in that embodiment.

Of course, as pointed out in the Official Action, Seki, et al. does mention in [0055] use of oxygen plasma followed by fluorine-based gas treatment (which is also discussed, e.g., in the 9th embodiment [0268]-[0269] (oxygen gas followed by CF₄)) however, Applicants respectfully submit that such an embodiment provides *no suggestion of modifying Seki, et al.'s 4th embodiment.*

It is further respectfully submitted that there has been no showing of any indication of motivation in the cited documents that would lead one having ordinary skill in the art to arrive at the above-discussed combination of claimed features.

The dependent claims are also submitted to be patentable because they set forth additional aspects of the present invention and are dependent from independent claims discussed above. Therefore, separate and individual consideration of each dependent claim is respectfully requested.

Applicants submit that this application is in condition for allowance, and a Notice of Allowance is respectfully requested.

Applicants' undersigned attorney may be reached in our Washington, D.C. office by telephone at (202) 530-1010. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,

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